

**Notice of References Cited**

Application/Control No.

09/989,850

Applicant(s)/Patent Under

Reexamination

ABADEER ET AL

Examiner

Dao H Nguyen

Art Unit

2818

Page 1 of 1

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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**INFORMATION DISCLOSURE CITATION***(Use several sheets if necessary)*

ATTY DOCKET NO.

BUR920010031Us1

SERIAL NO.

Wagdi W. Abadeer et al.

FILING

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Docket Number (Optional)

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Application Number

Applicant(s)

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